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Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0095				
I _D (A)	120				
Configuration	Single				
Package	TO-263				



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



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N-Channel MOSFET	S

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Dunin Comment	T _C = 25 °C a		120		
Continuous Drain Current	T _C = 125 °C	l _D	73		
Continuous Source Current (Diode Conduc	ction) ^a	I _S	120	Α	
Pulsed Drain Current b		I _{DM}	480		
Single Pulse Avalanche Current		I _{AS}	73		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	266	mJ	
Maximum Dawar Discinction h	T _C = 25 °C	D	375	10/	
Maximum Power Dissipation b T _C = 1		P_{D}	125	W	
Operating Junction and Storage Temperat	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount c	R_{thJA}	40	°C/W		
Junction-to-Case (Drain)		R_{thJC}	0.4	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	$V_{GS} = 0$, $I_D = 250 \mu\text{A}$		-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0079	0.0095		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0190	Ω	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0250		
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	99	-	S	
Dynamic ^b							•	
Input Capacitance	C _{iss}			=	6915	8645		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	635	795	pF	
Reverse Transfer Capacitance	C _{rss}	1		-	280	350		
Total Gate Charge ^c	Qg			-	120	180		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 85 \text{ A}$	-	30	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1		-	28.5	-	1	
Gate Resistance	R _g		f = 1 MHz	0.25	0.7	2.3	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	21	32		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 0.6 \Omega$ $I_{D} \cong 85 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 2.5 \Omega$		-	24	36	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	52	78		
Fall Time ^c	t _f			-	16	24	1	
Source-Drain Diode Ratings and Characteristics b								
Pulsed Current ^a	I _{SM}			-	-	480	А	
Forward Voltage	V _{SD}	I _F	I _F = 85 A, V _{GS} = 0		0.9	1.5	V	

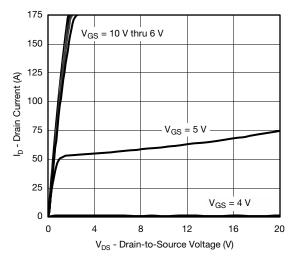
Notes

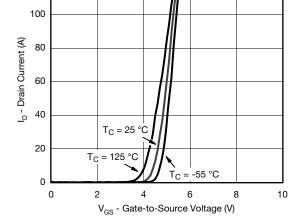
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



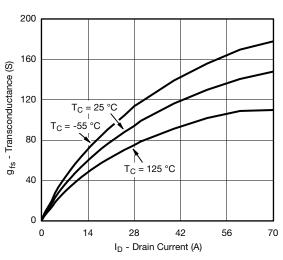
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

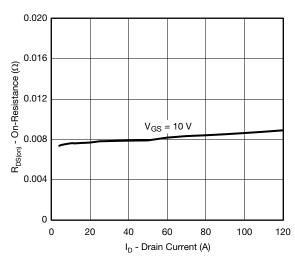




Output Characteristics

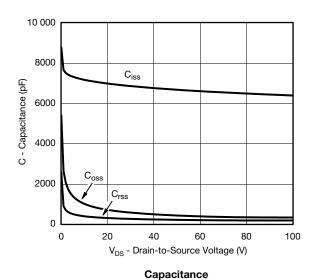


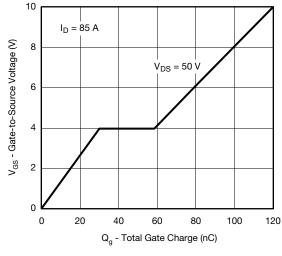




Transconductance

On-Resistance vs. Drain Current

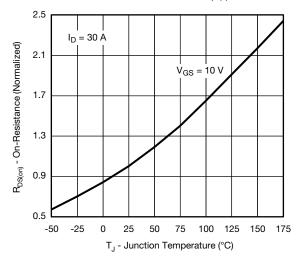




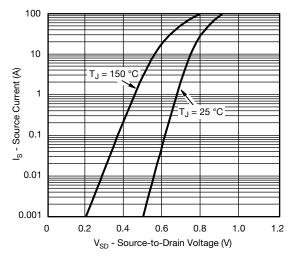
Gate Charge



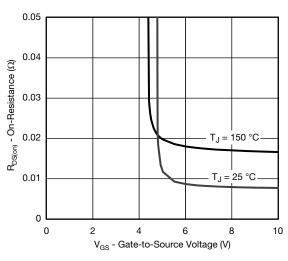
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



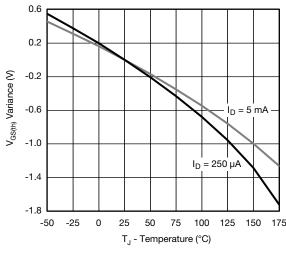
On-Resistance vs. Junction Temperature



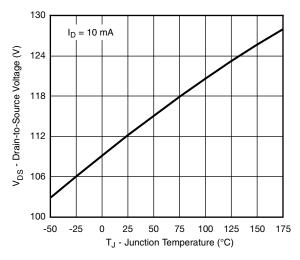
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



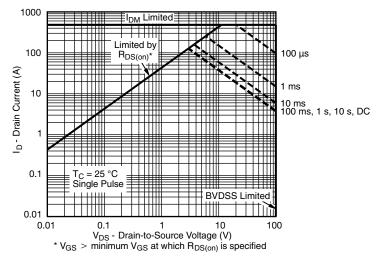
Threshold Voltage



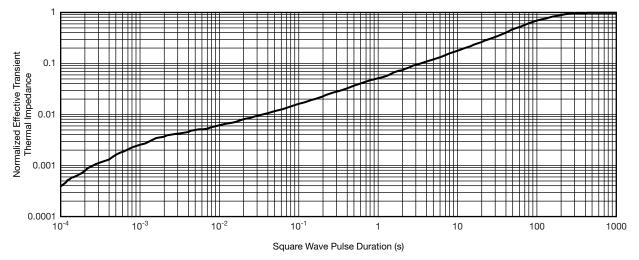
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



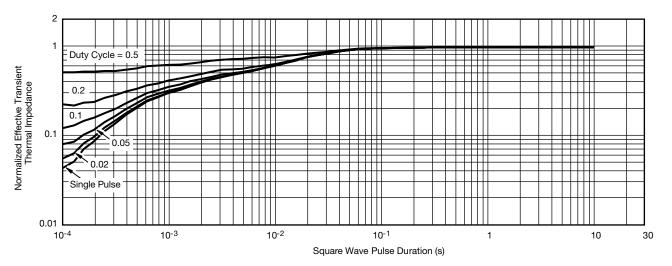
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg271515.



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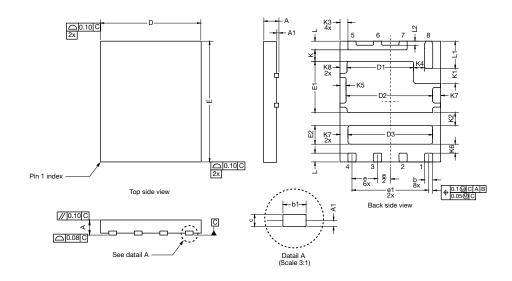
REVISION	REVISION HISTORY ^a					
REVISION	DATE	DESCRIPTION OF CHANGE				
С	04-Aug-15	Revised R _g minimum limit				

Note

a. As of April 2014



PowerPAIR® 6 x 5 F Case Outline



DIMENCION	MILLIMETERS			INCHES		
DIMENSION	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	-	0.10	0.000	-	0.004
b	0.35	0.41	0.46	0.014	0.016	0.018
b1		0.38 ref.			0.015 ref.	
С	0.15	0.20	0.25	0.006	0.008	0.010
D	4.90	5.00	5.10	0.193	0.197	0.201
D1	3.26	3.31	3.36	0.128	0.130	0.132
D2	4.20	4.30	4.40	0.165	0.169	0.173
D3	4.15	4.20	4.25	0.163	0.165	0.167
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	2.50	2.55	2.60	0.098	0.100	0.102
E2	0.87	0.92	0.97	0.034	0.036	0.038
е	1.27 BSC		0.050 BSC			
e1		3.81 BSC			0.150 BSC	
K	0.52	0.57	0.62	0.020	0.022	0.024
K1	0.69	0.74	0.79	0.027	0.029	0.031
K2	0.60	0.65	0.70	0.024	0.026	0.028
K3	0.39 BSC				0.015 BSC	
K4	0.50	0.55	0.60	0.020	0.022	0.024
K5	0.25	0.30	0.35	0.010	0.012	0.014
K6	0.40	0.45	0.50	0.016	0.018	0.020
K7	0.35	0.40	0.45	0.014	0.016	0.018
K8	0.30	0.35	0.40	0.012	0.014	0.016
L	0.33	0.43	0.53	0.013	0.017	0.021
L1	1.31	1.36	1.41	0.052	0.054	0.056
L2		0.20 ref.		0.008 ref.		

ECN: T20-0097-Rev. C, 25-Feb-2020

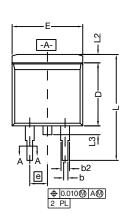
DWG: 6043

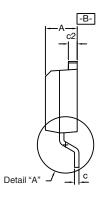
Note

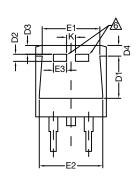
• Millimeters will govern



TO-263 (D²PAK): 3-LEAD

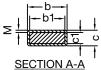








DETAIL A (ROTATED 90°)



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	SE	CTION	1	, †

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

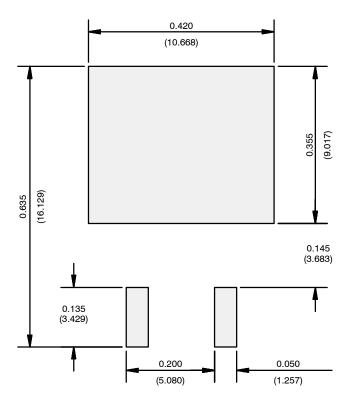
		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
	Α	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4 0.010		BSC	0.254	BSC	
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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